SUPPORTING INFORMATION

Thermoelectric Characteristics of Sb₂Te₃ Thin Films Formed via Surfactant-Assisted Electrodeposition

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Figure S1. XRD patterns of the Sb$_2$Te$_3$ films formed with and without CTAB.
Figure S2. TEM images (scale bar = 2 nm) of the Sb₂Te₃ films formed without CTAB: (a) before and (b) after annealing at 200 °C.